

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently amended) A method for classifying defects comprising:  
imaging an object by illuminating and scanning an electron beam and detecting  
with detectors;  
extracting images of a defect candidate from images obtained by each of said  
detectors at said imaging step and calculating defect information of said defect candidate, said  
calculated defect information including defect surface shape information, pattern defect  
information and voltage contrast defect information;  
classifying said extracted defect candidate image into a first category relating to  
criticality by using said calculated defect information;  
classifying said extracted defect candidate image into a second category relating  
to defect types; and  
displaying on a screen said extracted plural defect candidate ~~image~~ images side by  
side together with their first and second classification information, said first classification  
information relating to said first category, said second classification information relating to said  
second category,  
wherein said step of classifying said extracted defect candidate image into said  
second category is performed by comparing a circuit pattern area and a defect area, said circuit  
pattern area being obtained from a reference image and said defect area being obtained from said  
extracting step.

2-4. (Canceled)

5. (Currently amended) The method for classifying defects as described in  
claim ~~[[4]]~~ 1 wherein said defect type includes one or more of the following: particle defects,  
flaw defects, circuit pattern short defects, and circuit pattern open defects.

6. (Currently amended) A method for classifying defects comprising:  
imaging an object by illuminating and scanning an electron beam and detecting  
with detectors;  
extracting images of a defect candidate from images obtained from said detectors  
and calculating defect information of said defect candidate, said calculated defect information  
including defect surface shape information, pattern defect information and voltage contrast  
defect information;  
classifying said extracted defect candidate image into at least one defect type by  
using said calculated defect information;  
evaluating criticality of defect of said defect candidate image that has been  
classified into said at least one defect type; and  
displaying on a screen said extracted plural defect candidate ~~image~~ images side by  
side together with their first and second information, said first information relating to said  
classification of defect type, and said second information relating to said evaluation of said  
criticality of defect.

7. (Previously presented) The method for classifying defects as described in  
claim 6 wherein said imaging of said object is performed by illuminating and scanning an  
electron beam focused on said object and detecting, in synchronization with said scanning,  
secondary electrons generated from said object by said illumination.

8. (Original) The method for classifying defects as described in claim 6  
wherein said defect types for classification include one or more of the following: particle defects,  
flaw defects, circuit pattern short defects, and circuit pattern open defects.

9. (Currently amended) A method for classifying defects comprising:  
imaging an object by illuminating and scanning an electron beam and detecting  
with detectors;  
extracting defect candidates from images obtained by said detectors and  
calculating defect information of said defect candidate;

classifying said extracted defect candidate images into a first category relating to defect types by using said calculated defect information;

classifying said extracted defect candidate images into a second category relating to defect criticality, said second category relating to a predicted yield from said inspected object;  
and

displaying on a single screen a distribution on said inspected object of said defect candidates classified in said first category in a map format together with first and second classification information, said first classification information relating to said first category, said second information relating to said second category.

10. (Previously presented) The method for classifying defects as described in claim 9 wherein said imaging of said object is performed by illuminating and scanning an electron beam focused on said object and detecting, in synchronization with said scanning, secondary electrons generated from said object by said illumination.

11-22. (Canceled)

23. (Previously presented) The method for classifying defects as described in claim 1 further comprising forming an image based on said secondary electrons generated from said inspected object by said illumination.

24. (Previously presented) The method for classifying defects as described in claim 7 further comprising forming an image based on said secondary electrons generated from said inspected object by said illumination.

25. (Previously presented) The method for classifying defects as described in claim 10 further comprising forming an image based on said secondary electrons generated from said inspected object by said illumination.

26. (Canceled)

27. (Currently amended) The method for classifying defects as described in claim [[26]] 9 wherein said defect type includes particle defects, flaw defects, circuit pattern defects, and voltage contrast defects.

28-32. (Canceled)

33. (Previously presented) The method of claim 9, wherein said calculated defect information including defect surface shape information, pattern defect information and voltage contrast defect information.